

IN THE CLAIMS:

Please amend the claims as follows:

Claims 1-13 (Canceled)

Claim 14 (Previously Presented): A method of cutting an object to be processed, the method comprising:

a starting point region for cutting forming step of irradiating a wafer-like object to be processed with laser light while positioning a light-converging point within the object under a condition with a peak power density of at least 1×10^8 (W/cm²) at the light-converging point and a pulse width of 1 μ s or less, so as to form a modified region including a molten processed region within the object, and causing the modified region to form a starting point region for cutting, deviated from a center position of the object in a thickness direction thereof toward one end face of the object, along a line along which the object should be cut in the object; and

a pressing step of pressing the object from the other end face side of the object.

Claims 15-17 (Canceled)

Claim 18 (Previously Presented): A method of cutting an object to be processed, the method comprising:

a starting point region for cutting forming step of irradiating a wafer-like object to be processed which is made of a semiconductor material with laser light while positioning a light-converging point within the object, so as to form a molten processed region within the object,

and causing the molten processed region to form a starting point region for cutting, deviated from a center position of the object in a thickness direction thereof toward one end face of the object, along a line along which the object should be cut in the object; and

a pressing step of pressing the object from the other end face side of the object.

Claims 19-25 (Canceled)

Claim 26 (Previously Presented): A method of manufacturing a semiconductor device formed using a method of cutting an object to be processed, the manufacturing method comprising:

a starting point region for cutting forming step of irradiating a wafer-like object to be processed with laser light, the object comprising semiconductor material and having a surface formed with at least one semiconductor device, while positioning a light-converging point within the object under a condition with a peak power density of at least 1×10^8 (W/cm²) at the light-converging point and a pulse width of 1 μ s or less, so as to form a modified region including a molten processed region within the object, with the modified region forming a starting point region serving as a starting point for cutting, deviated from a center position of the object in a thickness direction thereof toward one end face of the object, the object along a line along which the object is to be cut; and

a pressing step of pressing the object from the other end face side of the object, with such pressing thereby resulting in cutting the object along the line along which the object is to be cut in order to provide at least one manufactured semiconductor device.

Claims 27 and 28 (Canceled)

Claim 29 (Previously Presented): A method of manufacturing a semiconductor device formed using a method of cutting an object to be processed, the manufacturing method comprising:

a starting point region for cutting forming step of irradiating a wafer-like object to be processed with laser light, the object comprising a semiconductor material and having a surface formed with at least one semiconductor device, while positioning a light-converging point within the object, so as to form a molten processed region within the object, with the molten processed region forming a starting point region serving as a starting point for cutting, deviated from a center position of the object in a thickness direction thereof toward one end face of the object, the object along a line along which the object is to be cut; and

a pressing step of pressing the object from the other end face side of the object, with such pressing thereby resulting in cutting the object along the line along which the object is to be cut in order to provide at least one manufactured semiconductor device.